

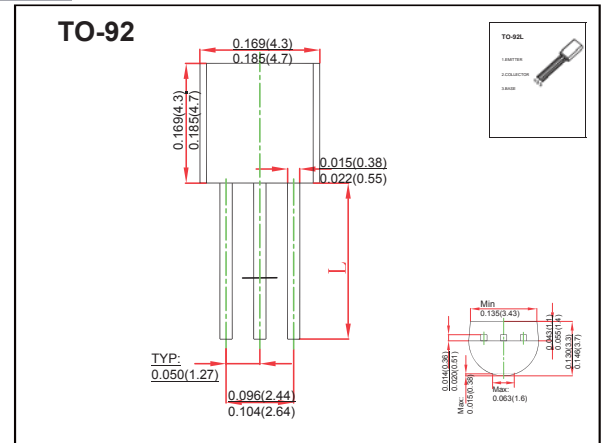
TO-92 Plastic-Encapsulate Transistors

FEATURE

- Power Switching Applications
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.8	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 ~ 150	°C

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
3DD13002B	TO-92	Bulk	1000pcs/Bag
3DD13002B-TA	TO-92	Tape	2000pcs/Box

Electrical Specification($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	M	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	600			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=600\text{V}, I_E=0$			100	μA
	I_{CEO}	$V_{CE}=400\text{V}, I_B=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			100	μA
Dc current gain	h_{FE1}	$V_{CE}=10\text{V}, I_C=200\text{mA}$			40	
	h_{FE2}	$V_{CE}=10\text{V}, I_C=0.25\text{mA}$				
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200\text{mA}, I_B=40\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=200\text{mA}, I_B=40\text{mA}$			1.1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}$ $f=1\text{MHz}$	5			MHz
Fall time	t_f	$I_C=1\text{A}, I_{B1}=-I_{B2}=0.2\text{A}$			0.5	μs
Storage time	t_s	$V_{CC}=100\text{V}$			2.5	μs

CLASSIFICATION OF h_{FE1}

Range	9-15	15-20	20-25	25-30	30-35	35-40

MARKING: 13002B

RATINGS AND CHARACTERISTIC CURVES

